ISC Audits & Reviews SC Summary (Jan 2018)

Doc.	Title	Result
5776A;	New Standard: Test Method and Acceptance Criteria for Visual Inspection of Surface Defects of GaN Epitaxial Wafers Used for Manufacturing HB-LED;	Passed
5800;	New Standard: Guide for Wafer Edge Trimming for 3DS-IC Process	Failed
6196;	Reapproval of SEMI C77-0912, Test Method for Determining the Counting Efficiency of Liquid-Borne Particle Counters for Which the Minimum Detectable Particle Size is Between 30 nm and 100 nm ;	Passed
6197;	Reapproval of SEMI F110-0712, Test Method for Mono-Dispersed Polystyrene Latex (PSL) Challenge of Liquid Filters;	Passed
6202;	Revision to SEMI E174-0817 SPECIFICATION FOR WAFER JOB MANAGEMENT (WJM);	Passed
6203;	Reapproval of SEMI T22-0212: Specification for Traceability by Self Authentication Service Body and Authentication Service Body;	Passed
6244;	Reapproval of SEMI T10-0701 (Reapproved 0912), Test Method For The Assessment Of 2d Data Matrix Direct Mark Quality ;	Passed
6246;	Reapproval of SEMI T17-0706 (Reapproved 0812), Specification Of Substrate Traceability ;	Passed
6247;	Reapproval of SEMI T18-1106 (Reapproved 0812), Specification of Parts And Components Traceability;	Passed
6264;	Reapproval of SEMI M8-0312 Specification for Polished Monocrystalline Silicon Test Wafers ;	Passed
6265;	Reapproval of SEMI M38-0312 Specification for Polished Reclaimed Silicon Wafers ;	Passed
6266;	Reapproval of SEMI MF110-1107 (Reapproved 0912) Test Method for Thickness of Epitaxial or Diffused Layers in Silicon by the Angle Lapping and Staining Technique ;	Passed
6267;	Reapproval of SEMI MF1188-1107 (Reapproved 0912) Test Method for Interstitial Oxygen Content of Silicon by Infrared Absorption With Short Baseline;	Passed
6268;	Reapproval of SEMI MF1388-0707 (Reapproved 0412) Test Method for Generation Lifetime and Generation Velocity of Silicon Material by Capacitance-Time Measurements of Metal-Oxide-Silicon (MOS) Capacitors;	Passed
6269;	Reapproval of SEMI MF1392-0307 (Reapproved 0512) Test Method for Determining Net Carrier Density Profiles in Silicon Wafers by Capacitance-Voltage Measurements with a Mercury Probe;	Passed
6271;	Reapproval of SEMI MF1569-0307 (Reapproved 0512) Guide for Generation of Consensus Reference Materials for Semiconductor Technology;	Passed
6272;	Reapproval of SEMI MF950-1107 (Reapproved 0912) Test Method For Measuring The Depth Of Crystal Damage Of A Mechanically Worked Silicon Wafer Surface By Angle Polishing And Defect Etching;	Passed
6273;	Reapproval of SEMI MF1619-1107 (Reapproved 0912) Test Method for Measurement of Interstitial Oxygen Content of Silicon Wafers by Infrared Absorption Spectroscopy with p-Polarized Radiation Incident at the Brewster Angle;	Passed

6274;	Reapproval of SEMI MF1630-1107 (Reapproved 0912) Test Method for Low Temperature FT-IR Analysis of Single Crystal Silicon for III-V Impurities;	Passed
6275;	Reapproval of SEMI MF2074-0912 Guide for Measuring Diameter of Silicon and Other Semiconductor Wafers;	Passed
6276;	Reapproval of SEMI MF374-0312 Test Method for Sheet Resistance of Silicon Epitaxial, Diffused, Polysilicon, and Ion-implanted Layers Using an In-Line Four-Point Probe with the Single-Configuration Procedure;	Passed
6277;	Reapproval of SEMI MF397-0812 Test Method for Resistivity of Silicon Bars Using a Two-Point Probe;	Passed
6278;	Reapproval of SEMI MF523-1107 (Reapproved 1012) Practice for Unaided Visual Inspection of Polished Silicon Wafer Surfaces;	Passed
6279;	Reapproval of SEMI MF525-0312 Test Method for Measuring Resistivity of Silicon Wafers Using a Spreading Resistance Probe;	Passed
6280;	Reapproval of SEMI MF576-0812 Test Method for Measurement of Insulator Thickness and Refractive Index on Silicon Substrates by Ellipsometry;	Passed
6281;	Reapproval of SEMI MF84-0312 Test Method For Measuring Resistivity Of Silicon Wafers With An In-Line Four-Point Probe;	Passed
6282;	Reapproval of SEMI MF671-0312 Test Method for Measuring Flat Length on Wafers of Silicon and Other Electronic Materials;	Passed
6283;	Reapproval of SEMI MF95-1107 (Reapproved 1012) Test Method For Thickness Of Lightly Doped Silicon Epitaxial Layers On Heavily Doped Silicon Substrates Using An Infrared Dispersive Spectrophotometer;	Passed
6287-LI2;	Add RELATED INFORMATION about SEMI E171 Predictive Carrier Logistics (PCL);	Passed
6288-LI1;	Addition of Table of Contents, and Removal of the list of section numbers and titles from section 2 and add a NOTE to explain replacement and relocation of the list.;	Passed
6292-LI1;	Change nonconforming title;	Passed
6293-LI1;	Change nonconforming title;	Passed
6293-LI2;	Add section title to meet the requirement which is specified section 3.2 of Procedure Manual;	Passed
R6125A;	Ratification Ballot - Revision to SEMI F23-0697 (Reapproved 0712), Particle Specification for Grade 10/0.2 Flammable Specialty Gases with title change to Specification for Particle Concentration of Grade 10/0.2 Hydrogen Gas;	Passed
R6204-LI1;	Ratification Ballot -Line Item Revision to SEMI S6-0707E - Environmental, Health, And Safety Guideline For Exhaust Ventilation Of Semiconductor Manufacturing Equipment (Changes to section 3.7.1);	Passed
SEMI S21-1106e	Editorial Changes to SEMI S21-1106E (Reapproved 0612), Safety Guideline For Worker Protection	Passed
SEMI F110-0712	Editorial Changes to SEMI F110-0712: Test Method For Mono-Dispersed Polystyrene Latex (PSL) Challenge Of Liquid Filters	Passed

Line Item (LI)

Doc. 5800 failed. All other documents passed and will be forwarded to Standards Publications for final processing.

For more information, please contact the SEMI Standards Engineer/Coordinator. (http://www.semi.org/standards/contacts) nearest you.

KN
V1
Jan 31, 2018